

ln. 7, change "damages" to -- damage -- ; and

ln. 9, after "disorder", insert -- is formed -- .

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A semiconductor device comprising a plurality of MOSFETs formed in a single semiconductor substrate,

each of the plurality of MOSFETs comprising:

a source region;

a drain region;

a channel forming region formed between the source region and the drain region; and

an impurity region being added with an impurity having an opposite conductive type to said source region and said drain region and being formed under said channel forming region, [and]

wherein a concentration of the impurity in the channel forming region is from 1/100 to 1/10 of that in said impurity region, and

wherein the impurity is introduced from a direction of the <110> axis with respect to the single semiconductor substrate.

NE 2. A device according to claim 1, wherein the concentration of the impurity in the impurity region is in a range of 1×10^{18} to 1×10^{19} atoms/cm³.

A2 3 (Amended). A device according to claim 1, wherein the concentration of the impurity in the impurity region is in a range of 1×10^{18} to 1×10^{19} atoms/cm³, and

wherein the impurity region is substantially not in contact with the source region and the drain region.

NE 4. A device according to claim 1, wherein the concentration of the impurity in the channel forming region is in a range of 1×10^{16} to 1×10^{17} atoms/cm³.

NE 14. A device according to claim 1, wherein each of the plurality of MOSFET further comprises a pair of LDD regions,
wherein one of the pair of LDD regions is formed between the source region and the channel forming region while the other of the pair of LDD regions is formed between the channel forming region and the drain region.

NE 15. A device according to claim 1, wherein said semiconductor device is an integrated circuit (IC).

NE 18. A device according to claim 1, wherein said semiconductor device is a microprocessor.

NE 21. A device according to claim 18, wherein said microprocessor is at least one selected from the group consisting of a RISC processor and an ASIC processor.

NE 24. A device according to claim 1, wherein said semiconductor device is at least one selected from the group consisting of a cellular phone, a personal handy phone system, and a portable computer.

Please add the following new claims:

Sub 27 -- 27. A device according to claim 1, wherein the impurity region is formed at a depth of from 20 to 150 nm from a surface of the single semiconductor substrate.--

-- 28. A device according to claim 1, wherein the single semiconductor substrate is a single silicon substrate.--

REMARKS

This amendment is in response to the Office Action of June 21, 1999 in the above-identified application.

Applicants are amending the specification and abstract to correct grammatical errors therein. It is believed that no new matter is being added. Applicants are also adding new Claim 27 (page 7 lines 26-28) and Claim 28 (page 1 line 3-5). The support in the specification is given in parenthesis. Accordingly, it is requested that each of these amendments be entered and allowed.

In the Office Action, the Examiner rejected Claims 1-4, 14-15, 18, 21 and 24 under 35 U.S.C. 103(a) as being unpatentable over Chang et al. This rejection is respectfully traversed.

The present invention, as recited in amended independent Claim 1, is directed to a semiconductor device including a channel forming region and an impurity region which is formed under the channel forming region, wherein an impurity with an opposite conductive type to a source region and a drain region is included in the channel forming region at a concentration of 1/100 to 1/10 compared with the impurity region, and wherein the impurity is introduced into the impurity region